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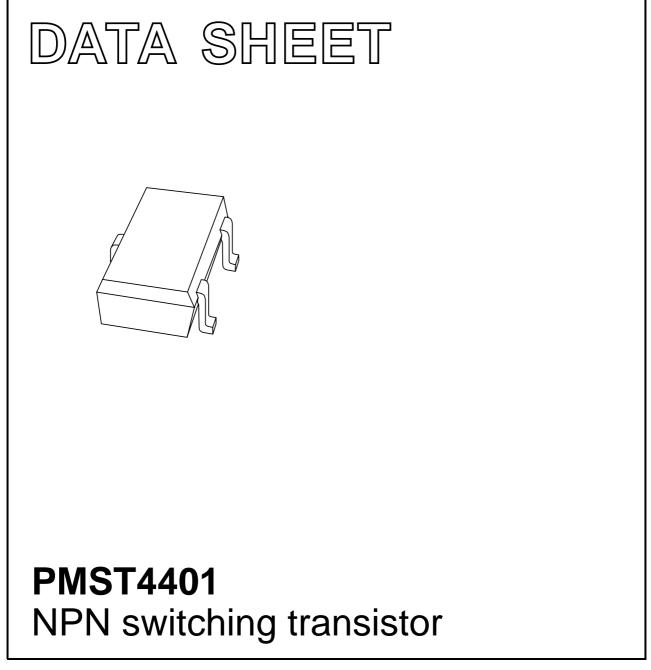
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 May 07 1999 Apr 22



Product data sheet

NPN switching transistor

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

• General purpose switching and linear amplification, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT323 plastic package. PNP complement: PMST4403.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾		
PMST4401	*2X		

Note

1. * = - : Made in Hong Kong.

* = t : Made in Malaysia.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

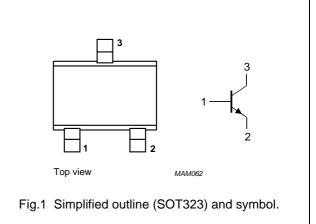
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current (DC)		-	600	mA
I _{CM}	peak collector current		-	600	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



PMST4401

NPN switching transistor

PMST4401

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

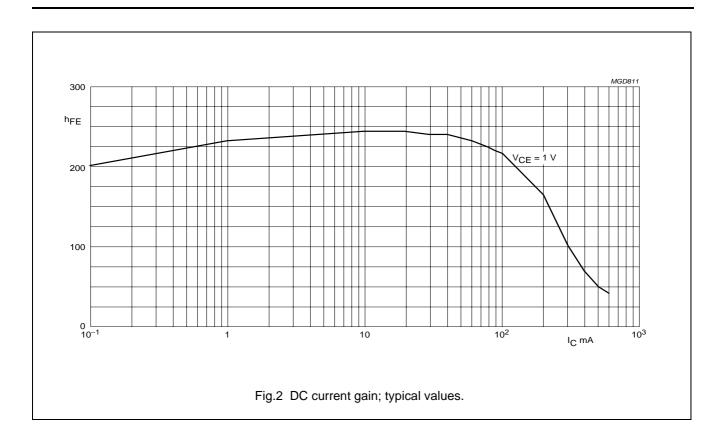
 T_{amb} = 25 °C unless otherwise specified.

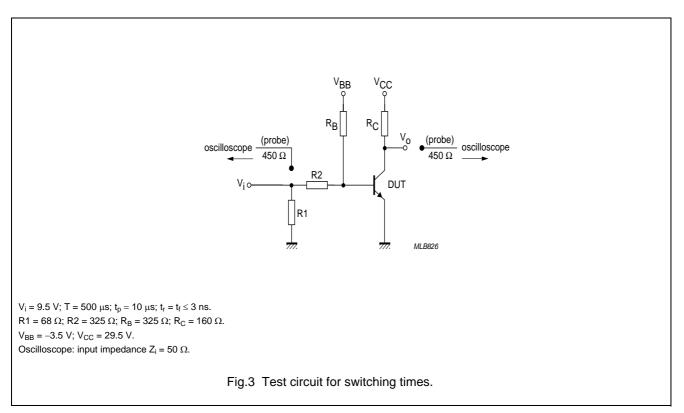
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 60 V	_	50	nA
		I _E = 0; V _{CB} = 60 V; T _j = 150 °C	_	10	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = 6 V$	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; (see Fig.2)			
		I _C = 0.1 mA	20	_	
		$I_{\rm C} = 1 \rm{mA}$	40	_	
		I _C = 10 mA	80	_	
		I _C = 150 mA; note 1	100	300	
	DC current gain	I _C = 500 mA; V _{CE} = 2 V; note 1	40	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	400	mV
		I _C = 500 mA; I _B = 50 mA; note 1	-	750	mV
V _{BEsat}	base-emitter saturation voltage	$I_{C} = 150 \text{ mA}; I_{B} = 15 \text{ mA}; \text{ note } 1$	_	950	mV
		$I_{\rm C} = 500 \text{ mA}; I_{\rm B} = 50 \text{ mA}; \text{ note } 1$	_	1.2	V
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 5 V; f = 1 MHz	_	8	pF
Ce	emitter capacitance	$I_E = i_e = 0; V_{EB} = 500 \text{ mV}; f = 1 \text{ MHz}$	_	30	pF
f _T	transition frequency	I _C = 20 mA; V _{CE} = 10 V; f = 100 MHz	250	-	MHz
Switching t	imes (between 10% and 90% levels); (see Fig.3)			
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	-	35	ns
t _d	delay time	I _{Boff} = –15 mA	_	15	ns
t _r	rise time	1	_	20	ns
t _{off}	turn-off time	1	_	250	ns
t _s	storage time	1	_	200	ns
t _f	fall time	1	_	60	ns

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

NPN switching transistor



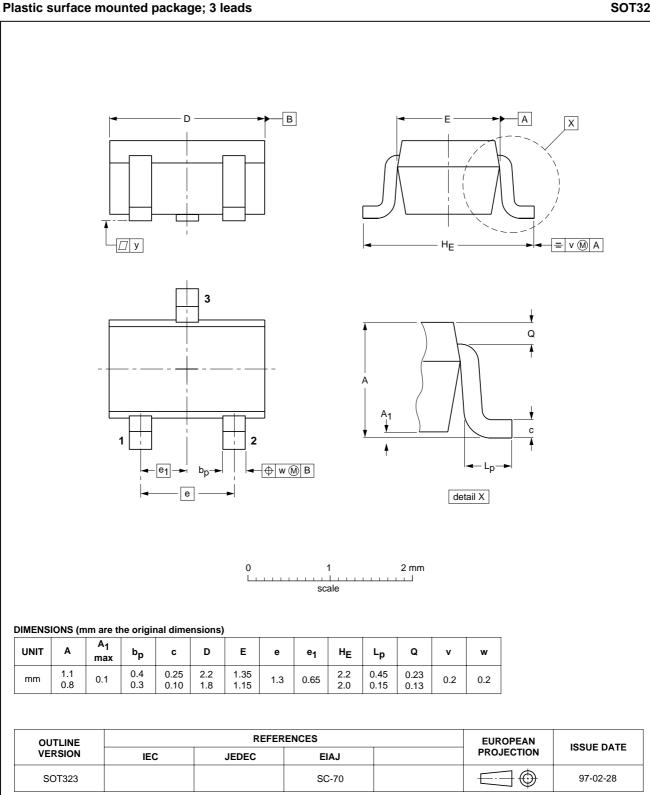


PMST4401

PMST4401

NPN switching transistor

PACKAGE OUTLINE



NPN switching transistor

PMST4401

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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